

20 V, dual P-channel Trench MOSFET 28 June 2016

Product data sheet

## 1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low leakage current
- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance  $R_{DSon}$  = 1.02  $\Omega$

## 3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Qu	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage	_		-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-	-500	mA
Static charac	cteristics (per transistor)			1	1		-
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -500 mA; T <sub>j</sub> = 25 °C		-	1.02	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa260
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

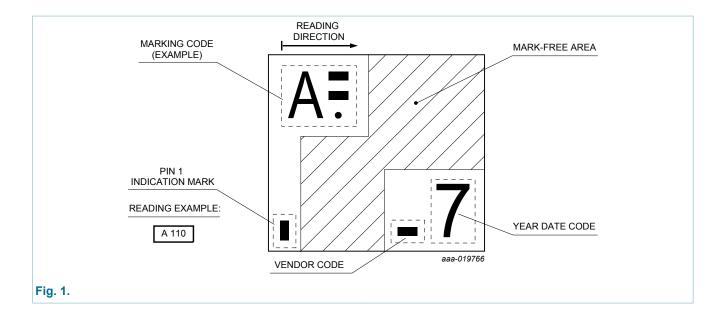
# 6. Ordering information

Table 3.   Ordering information							
Type number Package							
	Name	Description	Version				
PMDXB950UPEL	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216				

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMDXB950UPEL	B 111

#### 20 V, dual P-channel Trench MOSFET



# 8. Limiting values

#### Table 5.Limiting values

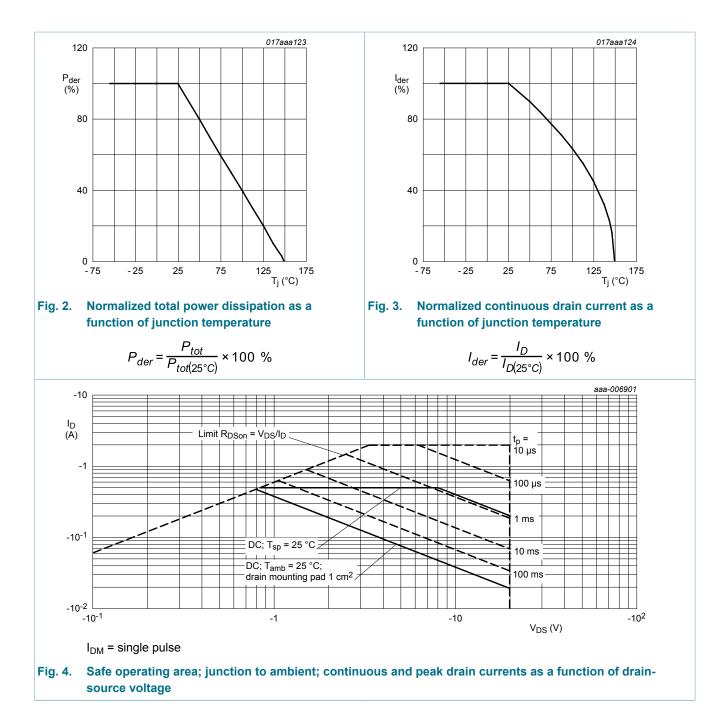
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-500	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-300	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	265	mΝ
			[1]	-	380	mΝ
		T <sub>sp</sub> = 25 °C		-	4025	m₩
Per device			1			
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	,	1	1	1	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-350	mA

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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## 9. Thermal characteristics

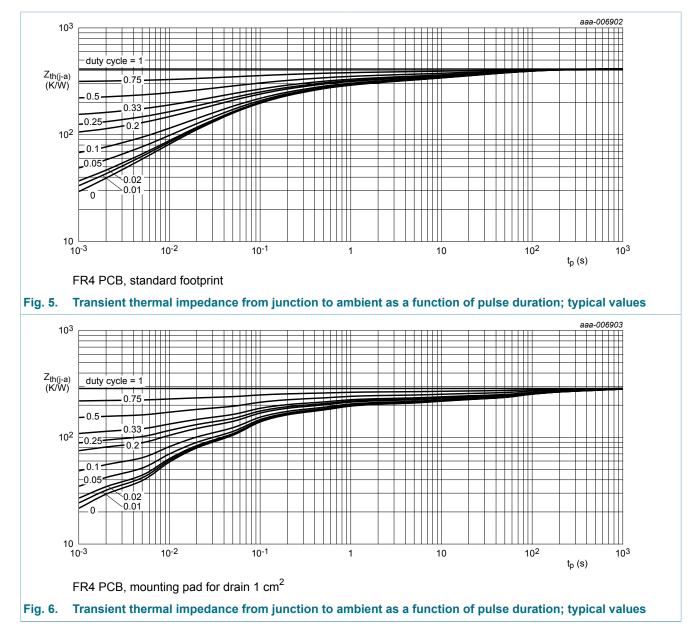
Table 6.       Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	410	475	K/W	
		[2]	-	285	330	K/W		

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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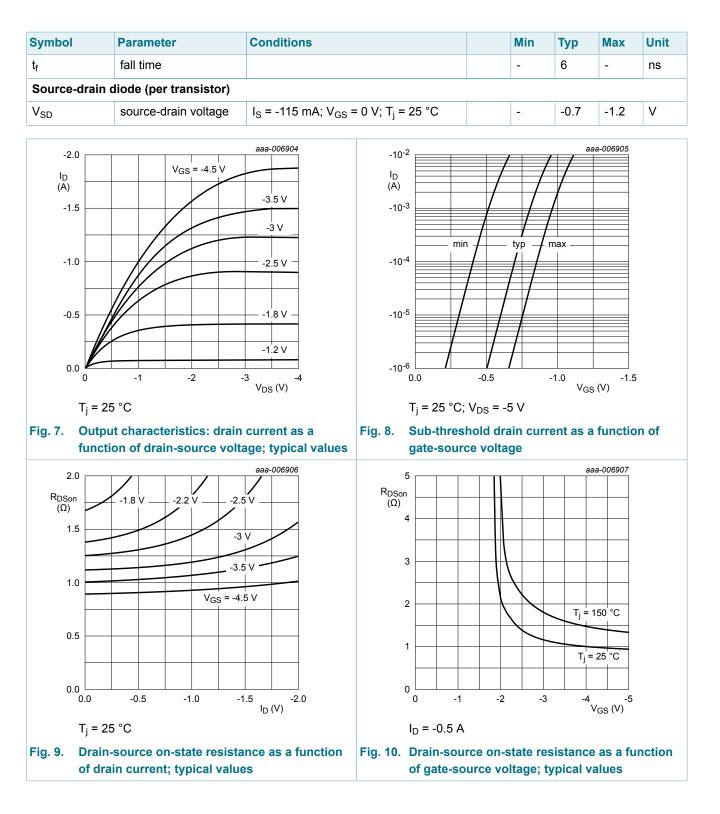
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics (per transistor)					_
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = -250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μA
		$V_{DS}$ = -5 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-25	nA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS}$ = -8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 1.8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	50	nA
		V <sub>GS</sub> = -1.8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-50	nA
R <sub>DSon</sub> drain-source of resistance	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -500 mA; T <sub>j</sub> = 25 °C	-	1.02	1.4	Ω
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -500 mA; T <sub>j</sub> = 150 °C	-	1.54	2.1	Ω
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -200 mA; T <sub>j</sub> = 25 °C	-	1.27	2.2	Ω
		$V_{GS}$ = -1.8 V; I <sub>D</sub> = -40 mA; T <sub>j</sub> = 25 °C	-	1.7	3.3	Ω
		$V_{GS}$ = -1.5 V; I <sub>D</sub> = -10 mA; T <sub>j</sub> = 25 °C	-	2.3	5	Ω
		$V_{GS}$ = -1.2 V; I <sub>D</sub> = -1 mA; T <sub>j</sub> = 25 °C	-	3.5	-	Ω
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -500 mA; T <sub>j</sub> = 25 °C	-	480	-	mS
Dynamic ch	aracteristics (per transist	or)	I	1		
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -450 mA;	-	1.19	2.1	nC
Q <sub>GS</sub>	gate-source charge	V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	0.17	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	43	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	14	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	8	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; I <sub>D</sub> = -0.45 A; R <sub>L</sub> = 22 Ω;	-	2.3	-	ns
t <sub>r</sub>	rise time	$V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 Ω; $T_j$ = 25 °C	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.5	-	ns

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# PMDXB950UPEL

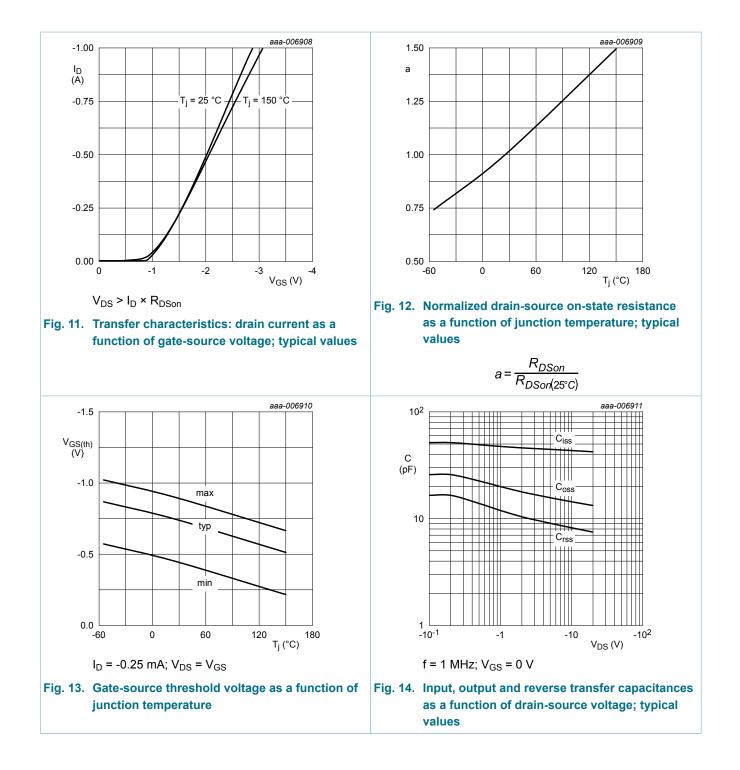
#### 20 V, dual P-channel Trench MOSFET



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## PMDXB950UPEL

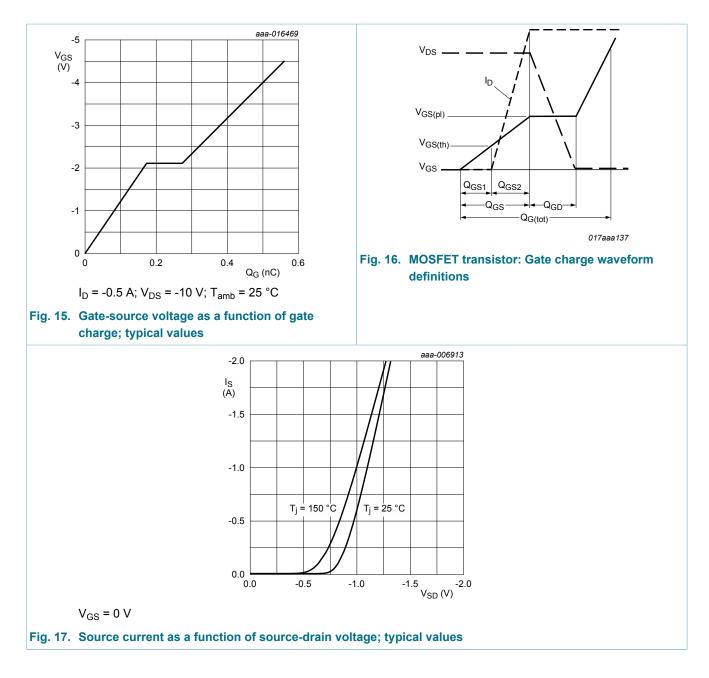
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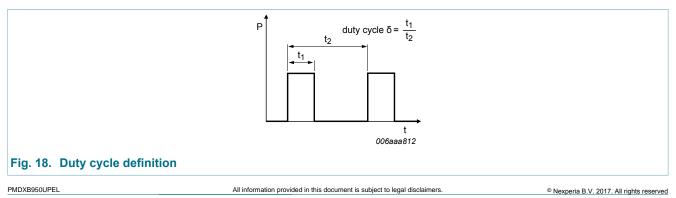
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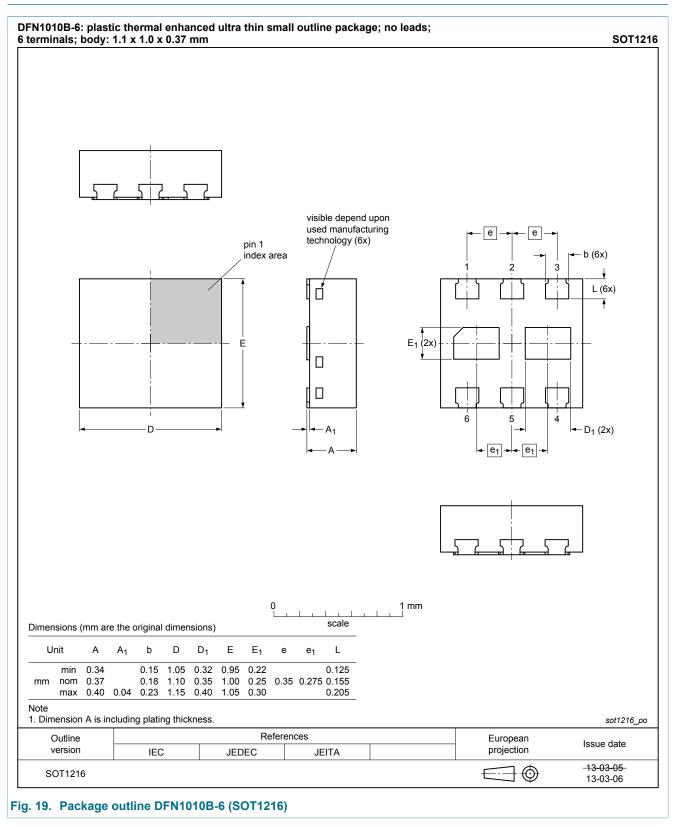
## 20 V, dual P-channel Trench MOSFET



# **11. Test information**



## 12. Package outline

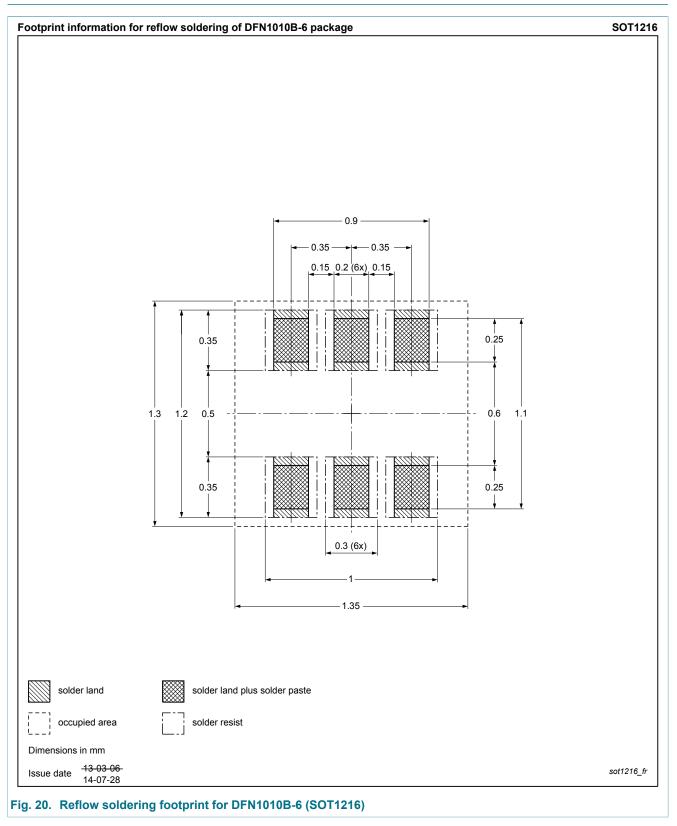


PMDXB950UPEL

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## 13. Soldering



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMDXB950UPEL v.1	20160628	Product data sheet	-	-		

#### 20 V, dual P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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